ABSTRACT

SEMICONDUCTOR MEMORY DEVICE AND METHOD OF MANUFACTURING THE SAME

A semiconductor memory device, and a method of manufacturing the semiconductor memory device are provided. The semiconductor memory device includes a first source layer, a second source layer on the first source layer, a stack on the second source layer, a channel structure passing through the stack and the second source layer, and a common source line passing through the stack and the second source layer. The second source layer includes an air gap and a conductive layer surrounding the air gap.

FIG. 1B